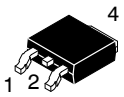
MOSFET – N-Channel Shielded Gate POWERTRENCH®

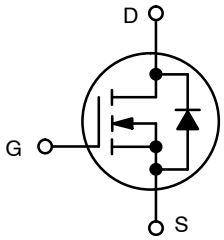
150 V, 15 mΩ, 61.3 A

NVDS015N15MC

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
150 V	15 mΩ @ 10 V	61.3 A



DPAK
CASE 369C



N−CHANNEL MOSFET

Features

- Shielded Gate MOSFET Technology
- Max $R_{DS(on)}$ = 15 mΩ at V_{GS} = 10 V, I_D = 29 A
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Primary Side for 48 V Isolated Bus
- SR for MV Secondary Applications

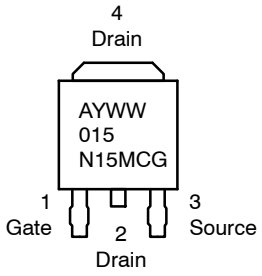
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter			Value	Unit
V_{DSS}	Drain−to−Source Voltage			150	V
V_{GS}	Gate−to−Source Voltage			±20	V
I_D	Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	61.3	A
			T_C = 100°C	43.4	
P_D	Power Dissipation $R_{\theta JC}$ (Note 2)		T_C = 25°C	107.1	W
			T_C = 100°C	53.6	
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	10.5	A
			T_A = 100°C	7.4	
P_D	Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	3.1	W
			T_A = 100°C	1.6	
I_{DM}	Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		382	A
T_J, T_{stg}	Operating Junction and Storage Temperature Range			−55 to +175	°C
I_S	Source Current (Body Diode)			89.3	A
E_{AS}	Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 4.4 A)			1301	mJ
T_L	Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

MARKING DIAGRAM



015N15MCG = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NVDS015N15MCT4G	DPAK (Pb−Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction−to−Case − Steady State (Note 2)	1.4	°C/W
$R_{\theta JA}$	Junction−to−Ambient − Steady State (Notes 1, 2)	47.9	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
$V_{(BR)DSS}$	Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA		150			V
$V_{(BR)DSS}/T_J$	Drain−to−Source Breakdown Voltage Temperature Coefficient	I_D = 250 μA, ref to 25°C			83		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 120 V	T_J = 25°C			1.0	μA
			T_J = 125°C		1.1		
I_{GSS}	Gate−to−Source Leakage Current	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
$V_{GS(TH)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 162 μA		2.5		4.5	V
$V_{GS(TH)}/T_J$	Negative Threshold Temperature Coefficient	I_D = 162 μA, ref to 25°C			−8.2		mV/°C
$R_{DS(on)}$	Drain−to−Source On Resistance	V_{GS} = 10 V, I_D = 29 A			11.8	15	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 29 A			58		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
C_{ISS}	Input Capacitance	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 75 V			2120		pF
C_{OSS}	Output Capacitance				595		
C_{RSS}	Reverse Transfer Capacitance				10.5		
$Q_{G(TOT)}$	Total Gate Charge	V_{GS} = 10 V, V_{DS} = 75 V; I_D = 29 A			27		nC
$Q_{G(TH)}$	Threshold Gate Charge				7		
Q_{GS}	Gate−to−Source Charge				11		
Q_{GD}	Gate−to−Drain Charge				4		
V_{GP}	Plateau Voltage				5.5		V
SWITCHING CHARACTERISTICS (Note 3)							
$t_{d(ON)}$	Turn−On Delay Time	V_{GS} = 10 V, V_{DD} = 75 V, I_D = 29 A, R_G = 6 Ω			16		ns
t_r	Rise Time				5		
$t_{d(OFF)}$	Turn−Off Delay Time				21		
t_f	Fall Time				4		
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Forward Diode Voltage	V_{GS} = 0 V, I_S = 29 A	T_J = 25°C		0.89	1.2	V
t_{RR}	Reverse Recovery Time	V_{GS} = 0 V, V_{DD} = 75 V dI_S/dt = 300 A/μs, I_S = 29 A			49		ns
Q_{RR}	Reverse Recovery Charge				197		nC
t_{RR}	Reverse Recovery Time	V_{GS} = 0 V, V_{DD} = 75 V dI_S/dt = 1000 A/μs, I_S = 29 A			34		ns
Q_{RR}	Reverse Recovery Charge				345		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

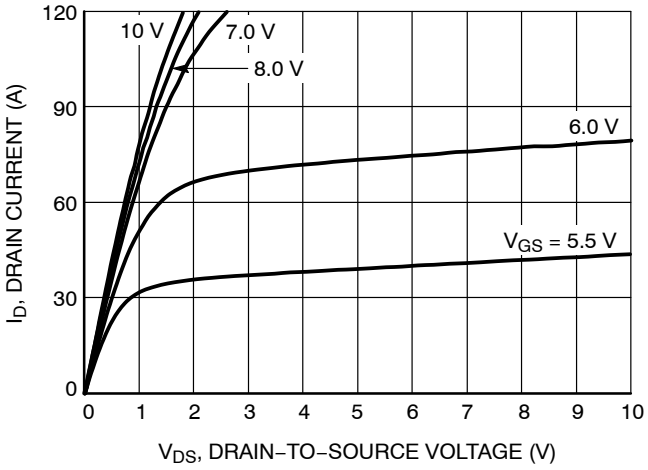


Figure 1. On−Region Characteristics

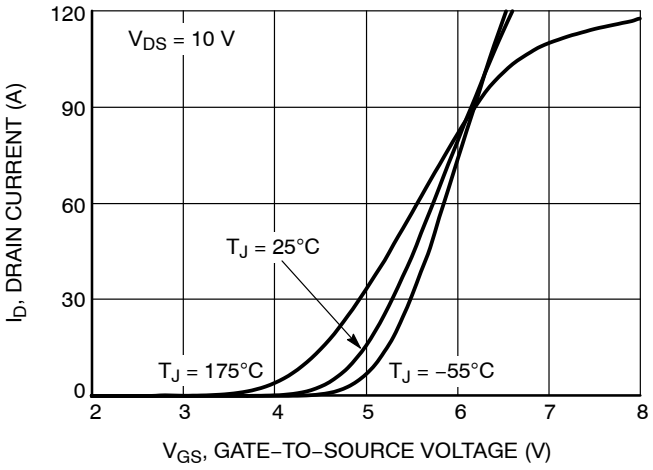


Figure 2. Transfer Characteristics

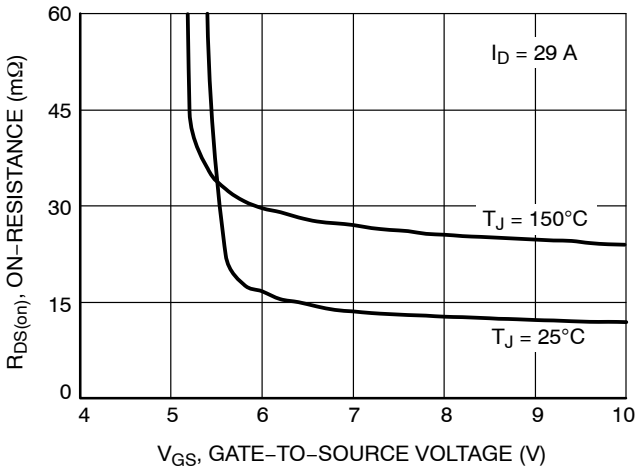


Figure 3. On−Resistance vs. Gate−to−Source Voltage

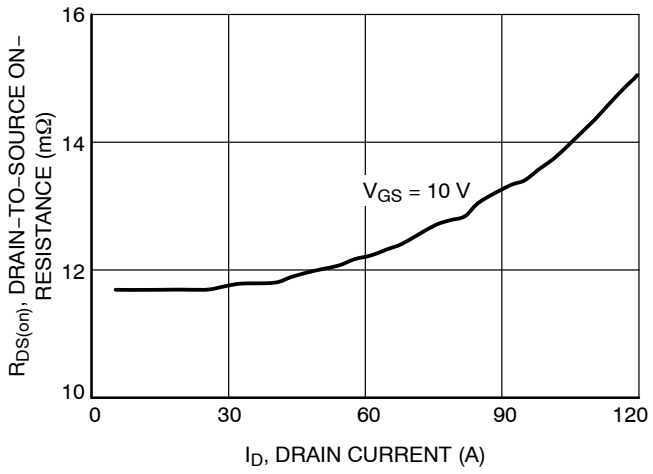


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

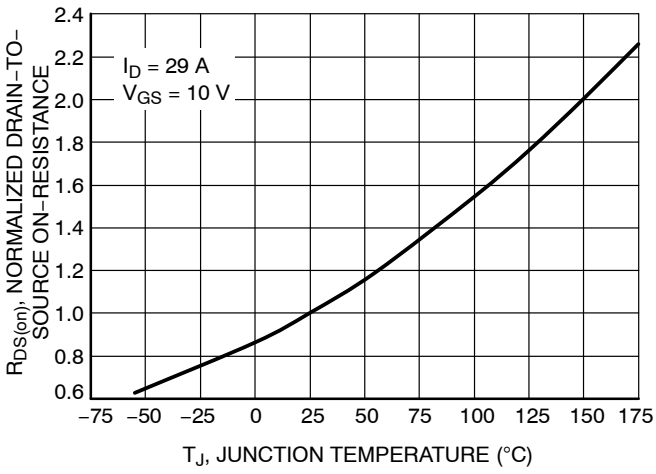


Figure 5. Normalized On−Resistance vs. Junction Temperature

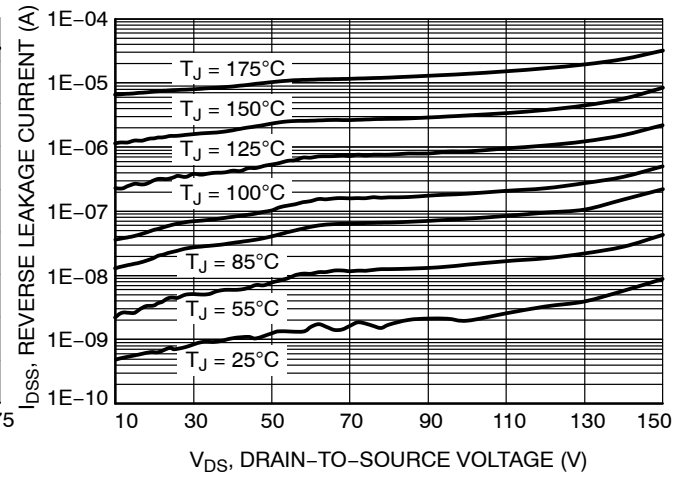


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continue)

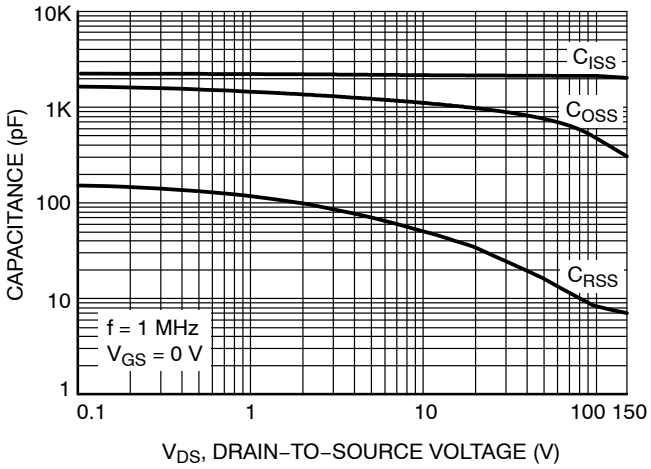


Figure 7. Capacitance vs. Drain−to−Source Voltage

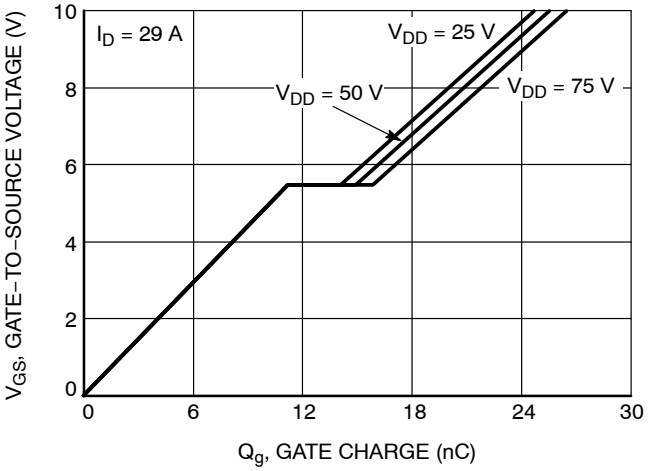


Figure 8. Gate Charge Characteristics

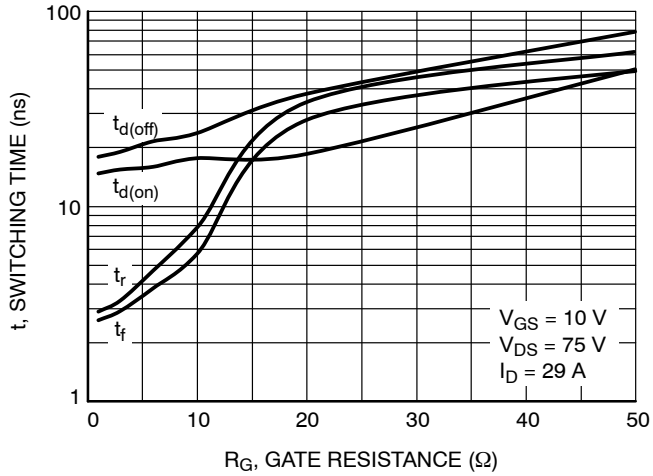


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

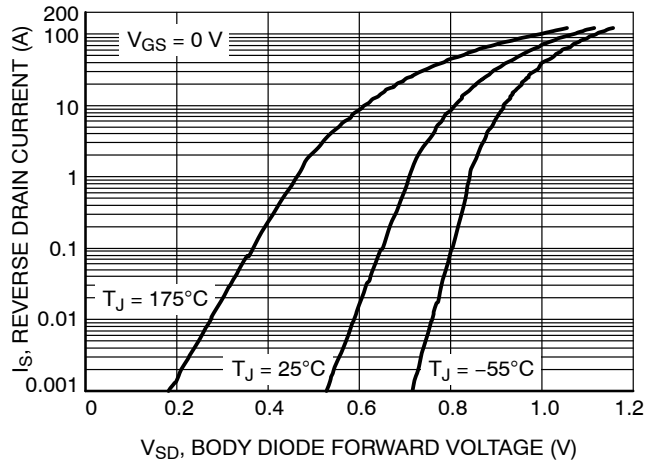


Figure 10. Source−to−Drain Diode Forward Voltage vs. Source Current

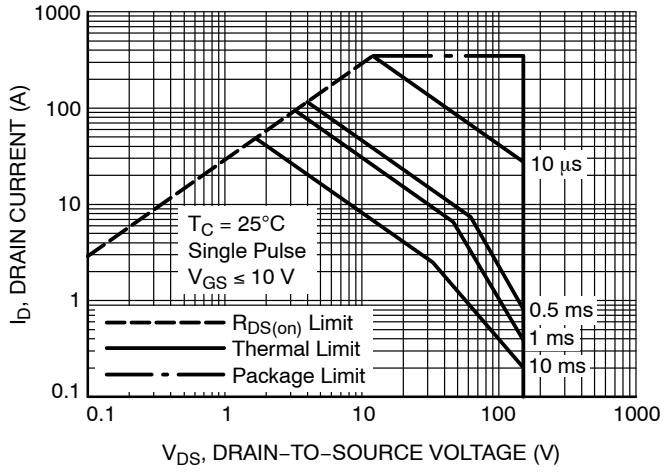


Figure 11. Forward Bias Safe Operating Area

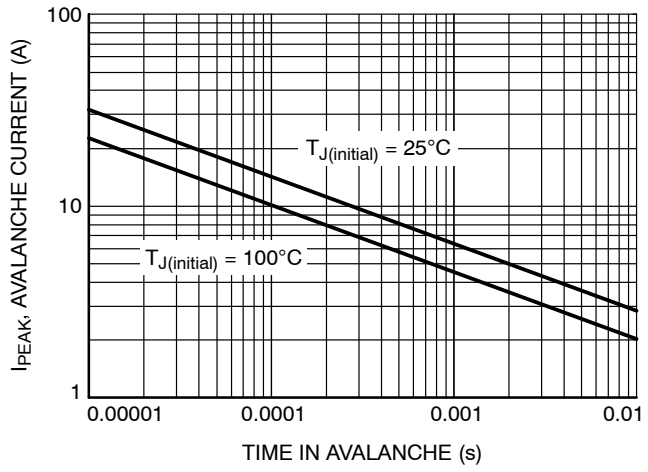


Figure 12. Unclamped Inductive Switching Capability

TYPICAL CHARACTERISTICS (continue)

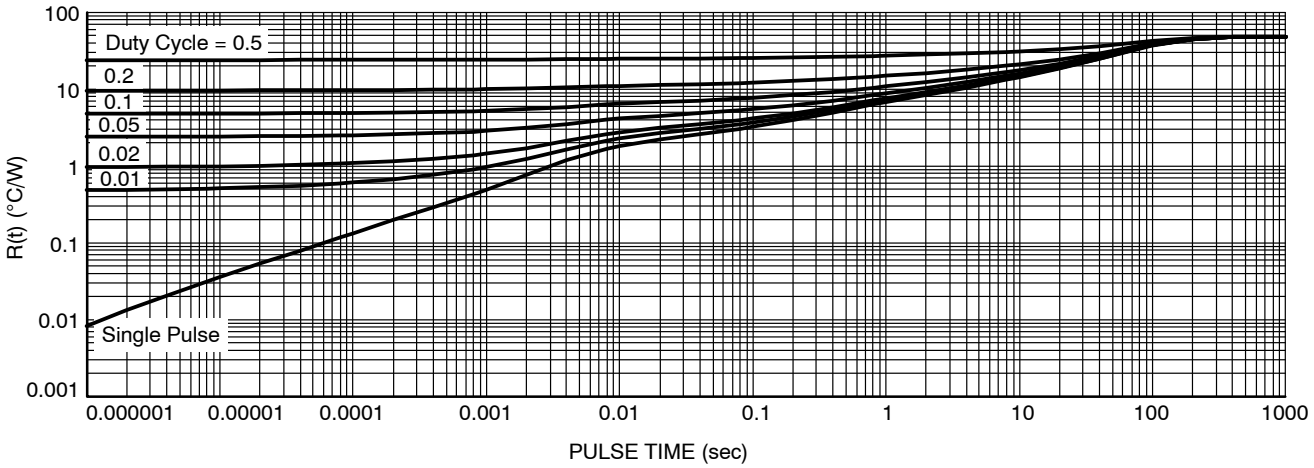
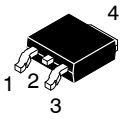


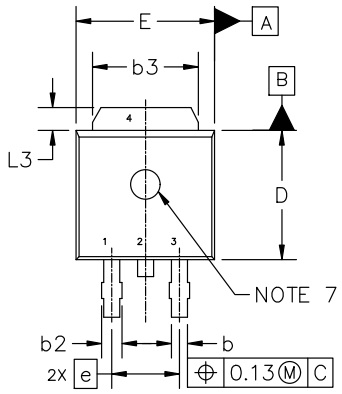
Figure 13. Transient Thermal Impedance



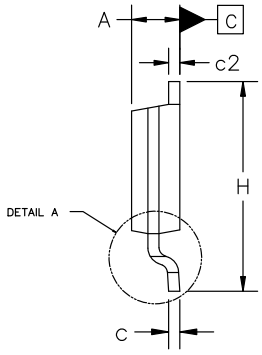
DPAK−3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE K

DATE 14 MAY 2026

SCALE 1:1

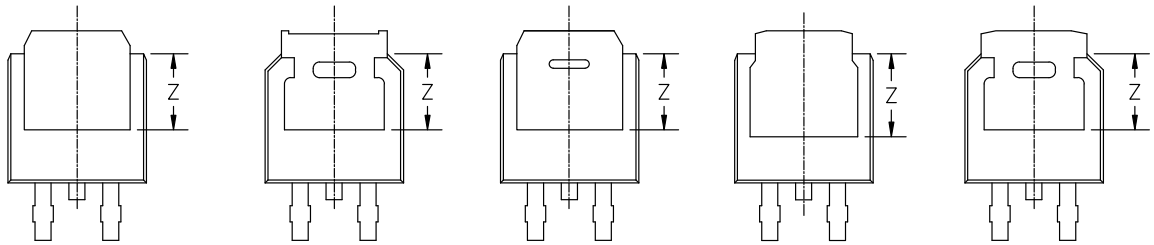


TOP VIEW



SIDE VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	2.18	2.28	2.38
A1	0.00	−−−	0.13
b	0.63	0.76	0.89
b2	0.72	0.93	1.14
b3	4.57	5.02	5.46
c	0.46	0.54	0.61
c2	0.46	0.54	0.61
D	5.97	6.10	6.22
E	6.35	6.54	6.73
e	2.29 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	−−−	1.27
L4	−−−	−−−	1.01
Z	3.93	−−−	−−−

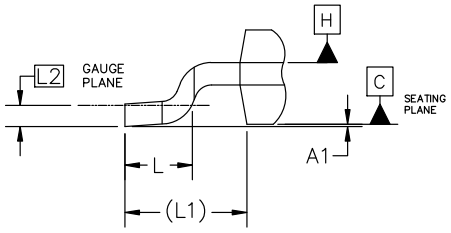


BOTTOM VIEW

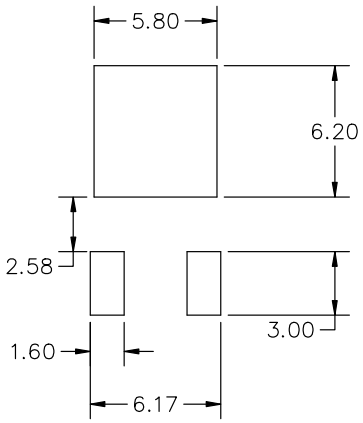
ALTERNATE CONSTRUCTIONS

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.



DETAIL A
ROTATED 90° CW



RECOMMENDED MOUNTING FOOTPRINT*

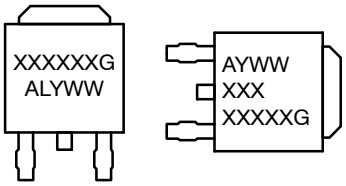
*FOR ADDITIONAL INFORMATION ON OUR PB−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON10527D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DPAK−3 6.10x6.54x2.28, 2.29P**	**PAGE 1 OF 2**

DPAK−3 6.10x6.54x2.28, 2.29P
CASE 369C
ISSUE K

DATE 13 MAY 2026

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX	= Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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